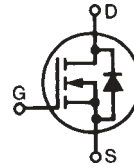


# PolarHT™ HiPerFET IXFK 140N20P

## Power MOSFET

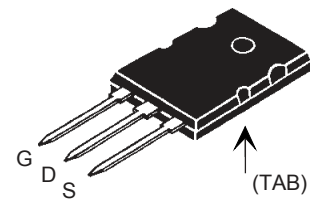
N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode

$V_{DSS} = 200 \text{ V}$   
 $I_{D25} = 140 \text{ A}$   
 $R_{DS(on)} \leq 18 \text{ m}\Omega$   
 $t_{rr} \leq 200 \text{ ns}$



Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C to } 175^\circ\text{C}$	200	V
$V_{DGR}$	$T_J = 25^\circ\text{C to } 175^\circ\text{C}; R_{GS} = 1 \text{ M}\Omega$	200	V
$V_{GS}$	Continuous	$\pm 20$	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	140	A
$I_{D(RMS)}$	External lead current limit	75	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	280	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	60	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	100	mJ
$E_{AS}$	$T_C = 25^\circ\text{C}$	4	J
$dv/dt$	$I_S \leq I_{DM}$ , $di/dt \leq 100 \text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ , $R_G = 4 \Omega$	10	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	830	W
$T_J$		-55 ... +175	$^\circ\text{C}$
$T_{JM}$		175	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
$T_{SOLD}$	Plastic body for 10 s	260	$^\circ\text{C}$
$M_d$	Mounting torque	1.13/10	Nm/lb.in.
<b>Weight</b>		10	g

TO-264 (IXFK)



G = Gate      D = Drain  
S = Source      TAB = Drain

### Features

- † International standard package
- † Unclamped Inductive Switching (UIS) rated
- † Low package inductance
  - easy to drive and to protect

### Advantages

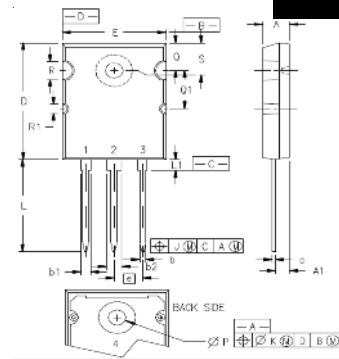
- † Easy to mount
- † Space savings
- † High power density

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$	200		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 4 \text{ mA}$	2.5		5.0 V
$I_{GSS}$	$V_{GS} = \pm 20 \text{ V}_{DC}$ , $V_{DS} = 0$			$\pm 200 \text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 150^\circ\text{C}$			25 $\mu\text{A}$ 250 $\mu\text{A}$
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$ , $I_D = 0.5 I_{D25}$ $V_{GS} = 15 \text{ V}$ , $I_D = 140 \text{ A}$ Pulse test, $t \leq 300 \mu\text{s}$ , duty cycle $d \leq 2 \%$	14		18 $\text{m}\Omega$ $\text{m}\Omega$

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{ V}$ ; $I_D = 0.5 I_{D25}$ , pulse test	50	84	S
$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$		7500	pF
$C_{oss}$			1800	pF
$C_{rss}$			280	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0.5 V_{DSS}$ , $I_D = 60\text{ A}$ $R_G = 3.3\ \Omega$ (External)		30	ns
$t_r$			35	ns
$t_{d(off)}$			150	ns
$t_f$			90	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0.5 V_{DSS}$ , $I_D = 0.5 I_{D25}$		240	nC
$Q_{gs}$			50	nC
$Q_{gd}$			100	nC
$R_{thJC}$				$0.18^\circ\text{C/W}$
$R_{thCS}$		0.15		$^\circ\text{C/W}$

**Source-Drain Diode**

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		Min.	Typ.	Max.
$I_s$	$V_{GS} = 0\text{ V}$			140 A
$I_{SM}$	Repetitive			280 A
$V_{SD}$	$I_F = I_s$ , $V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.5 V
$t_{rr}$	$I_F = 25\text{ A}$ $-di/dt = 100\text{ A}/\mu\text{s}$		120	200 ns
$Q_{RM}$		$V_R = 100\text{ V}$ , $V_{GS} = 0\text{ V}$		3.5

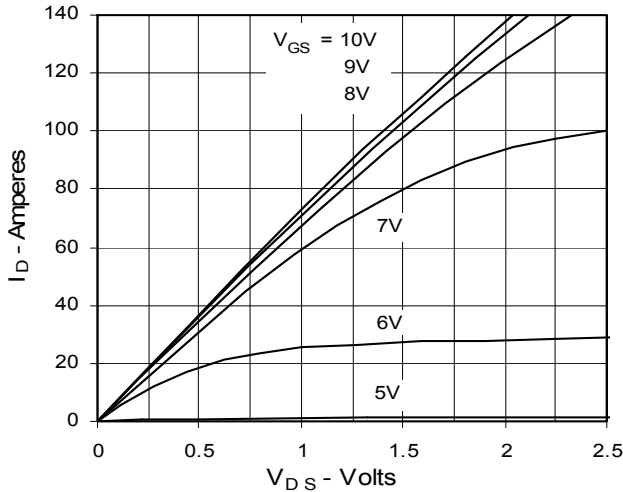
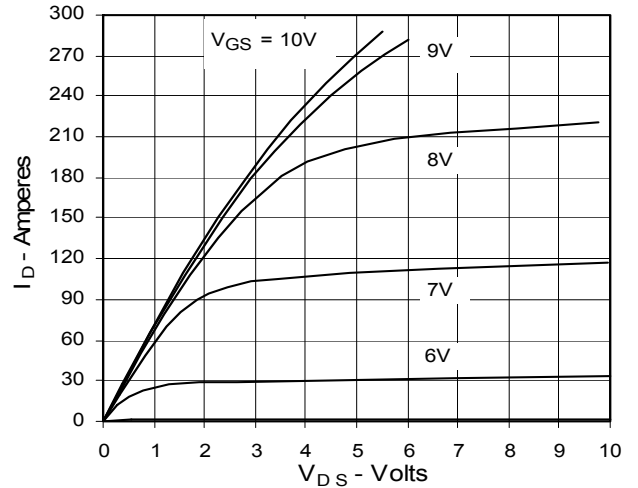
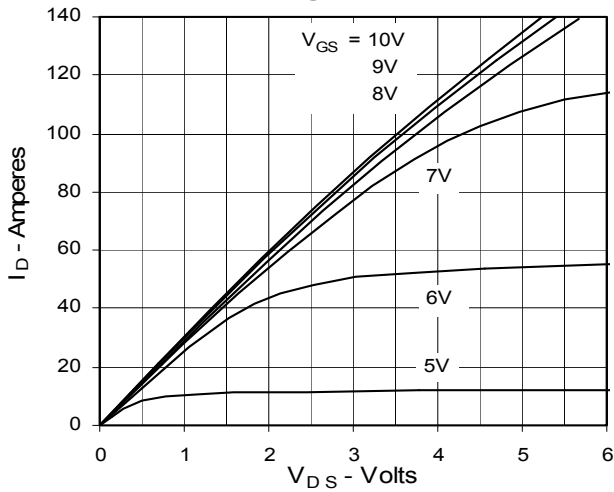
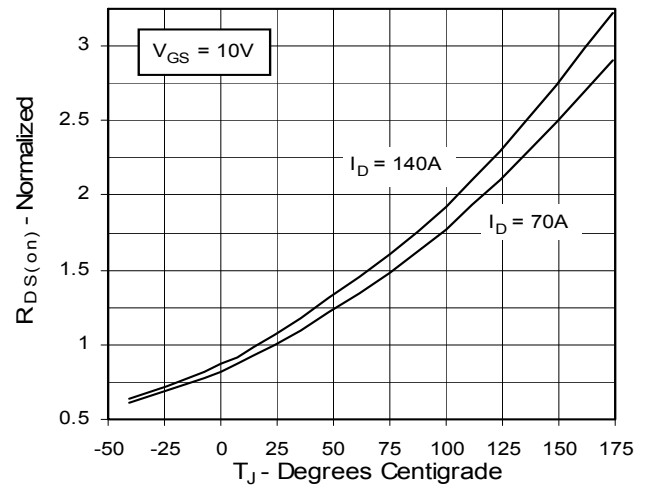
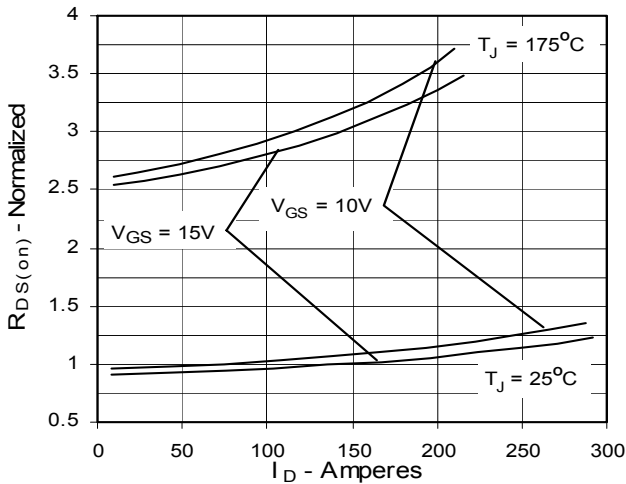
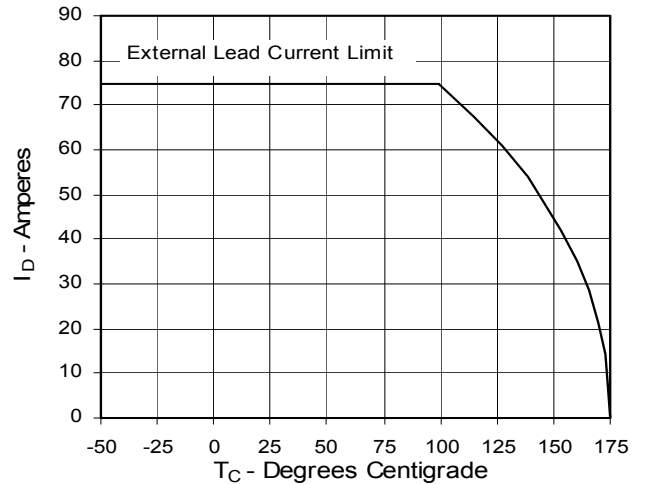
**TO-264 (IXFK) Outline**


- 1 - GATE
- 2, 4 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.70	5.31
A1	.102	.118	2.59	3.00
b	.037	.055	0.94	1.40
b1	.087	.102	2.21	2.59
b2	.110	.126	2.79	3.20
c	.017	.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	.760	.799	19.30	20.29
e	.215 BSC		5.46 BSC	
J	.000	.010	0.00	0.25
K	.000	.010	0.00	0.25
L	.779	.842	19.79	21.39
L1	.087	.102	2.21	2.59
$\varnothing P$	.122	.138	3.10	3.51
Q	.240	.256	6.10	6.50
Q1	.330	.346	8.38	8.79
$\varnothing R$	.155	.187	3.94	4.75
$\varnothing R1$	.085	.093	2.16	2.36
S	.243	.253	6.17	6.43

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405B2	6,759,692
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2

**Fig. 1. Output Characteristics  
@ 25°C**

**Fig. 2. Extended Output Characteristics  
@ 25°C**

**Fig. 3. Output Characteristics  
@ 150°C**

**Fig. 4.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$   
Value vs. Junction Temperature**

**Fig. 5.  $R_{DS(on)}$  Normalized to 0.5  $I_{D25}$   
Value vs. Drain Current**

**Fig. 6. Drain Current vs. Case Temperature**


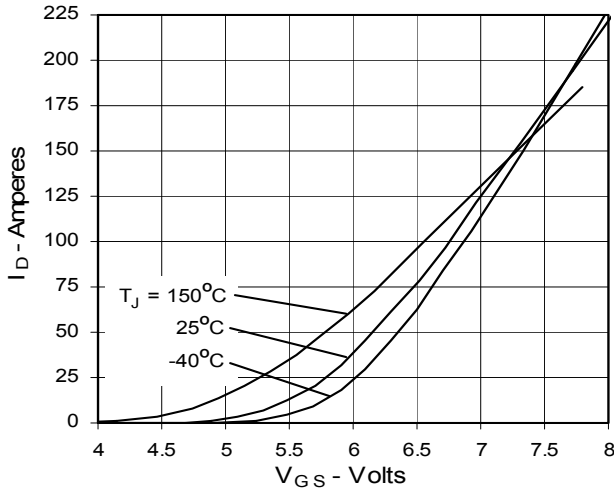
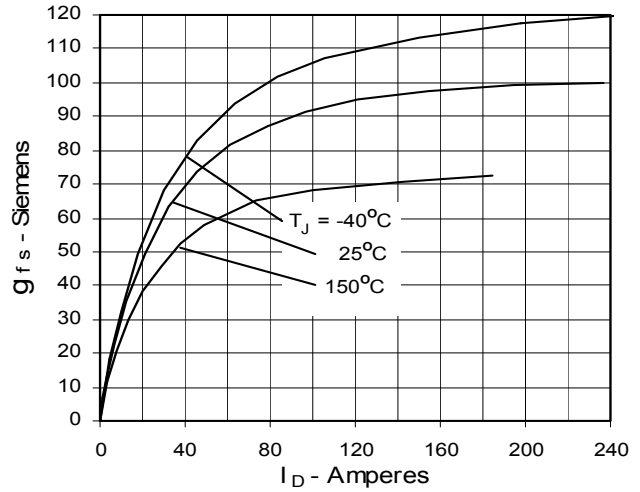
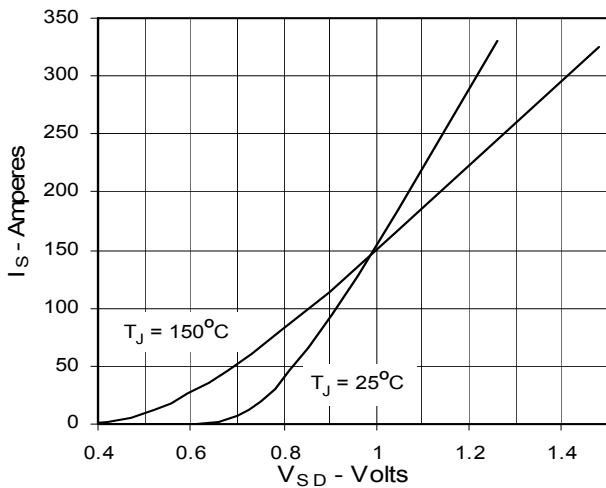
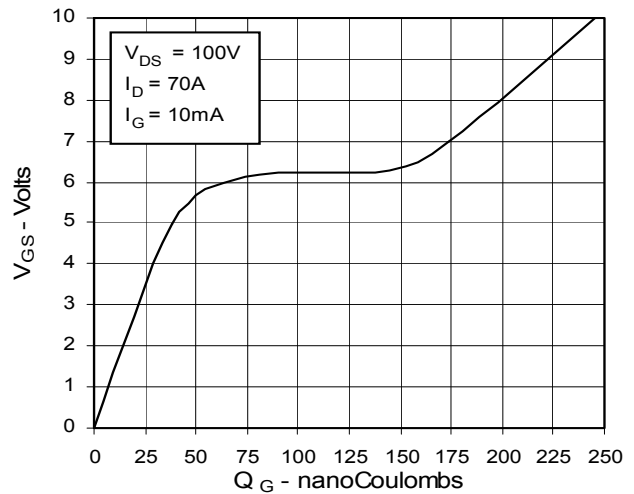
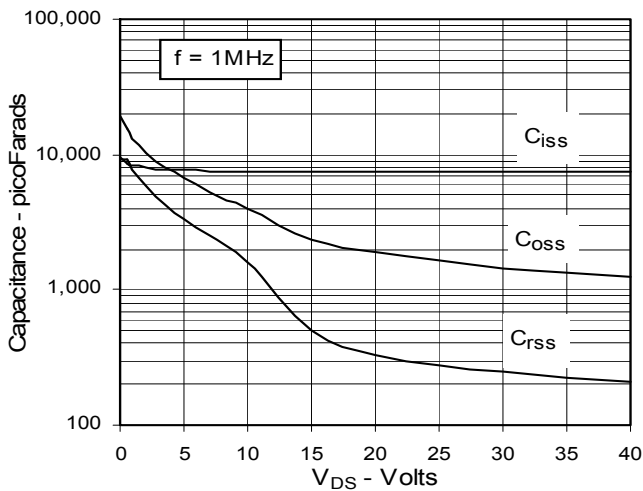
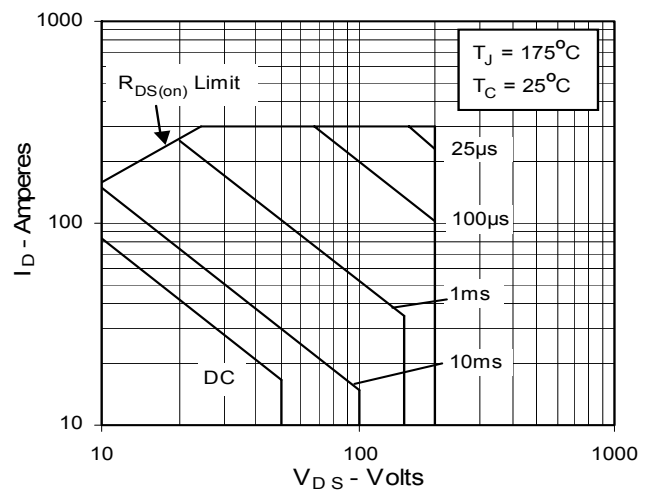
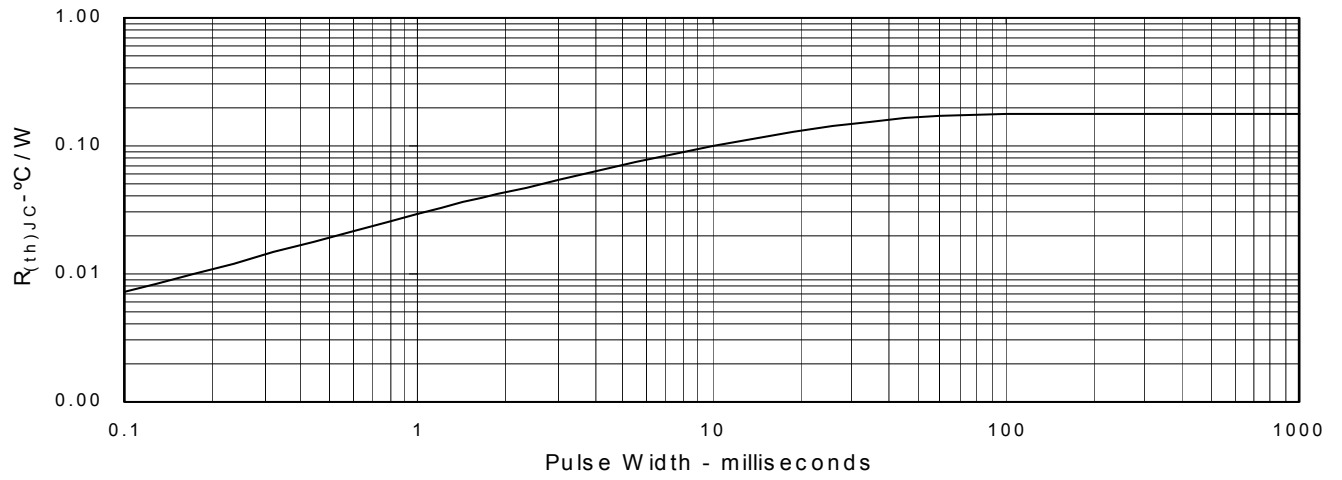
**Fig. 7. Input Admittance**

**Fig. 8. Transconductance**

**Fig. 9. Source Current vs. Source-To-Drain Voltage**

**Fig. 10. Gate Charge**

**Fig. 11. Capacitance**

**Fig. 12. Forward-Bias Safe Operating Area**


Fig. 13. Maximum Transient Thermal Resistance





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